

Electronic Supplementary Information

Controlled self-assembly of block copolymers in printed sub-20 nm cross-bar structures

Tae Wan Park,^{ab} Young Lim Kang,^c Myunghwan Byun,^d Suck Won Hong,^e Yong-Sik Ahn,^c Junghoon Lee^{f*} and Woon Ik Park^{c*}

^aElectronic Convergence Materials Division, Korea Institute of Ceramic Engineering & Technology (KICET) 101 Soho-ro, Jinju 52851, Republic of Korea.

^bDepartment of Materials Science and Engineering, Korea University, Seoul 02841, Republic of Korea.

^cDepartment of Materials Science and Engineering, Pukyong National University (PKNU), 45 Yongso-ro, Nam-gu, Busan 48513, Republic of Korea.

E-mail: thane0428@pknu.ac.kr

^dDepartment of Advanced Materials Engineering, Keimyung University, 1095 Dalgubeol-daero, Daegu 42601, Republic of Korea.

^eDepartment of Cogno-Mechatronics Engineering, Department of Optics and Mechatronics Engineering, College of Nanoscience and Nanotechnology, Pusan National University, Busan 46241, Republic of Korea.

^fDepartment of Metallurgical Engineering, Pukyong National University (PKNU), 45 Yongso-ro, Nam-gu, Busan 48513, Republic of Korea.

E-mail: jlee1@pknu.ac.kr

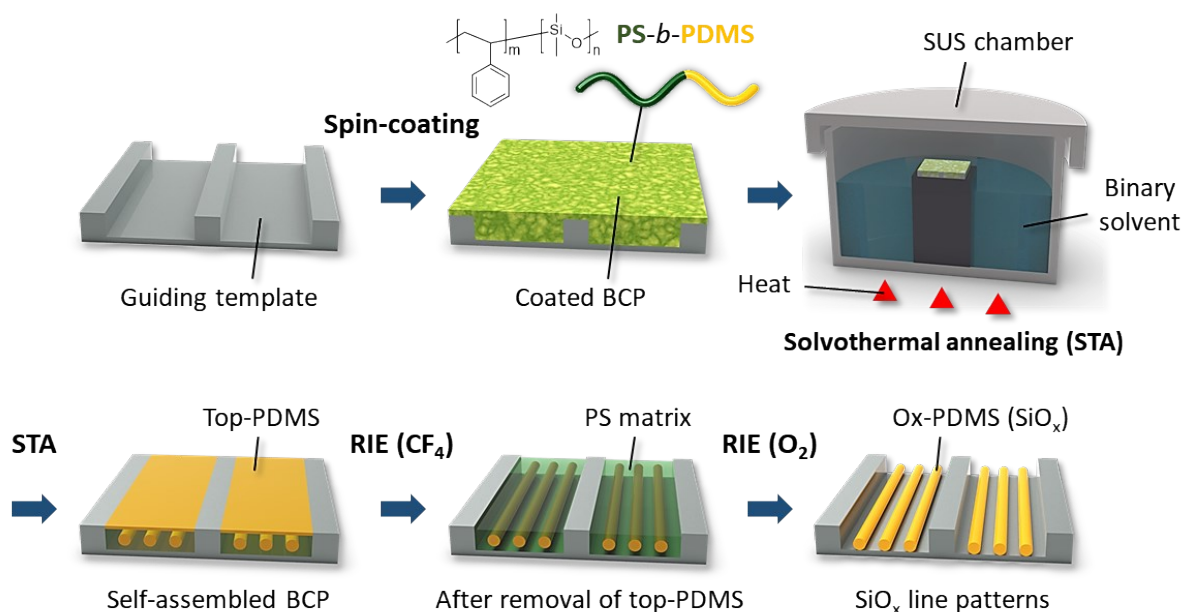


Fig. S1. Procedure for the pattern formation of sub-20 nm master mold by DSA of BCP. A cylinder-forming PS-*b*-PDMS BCP (SD45) is spin-coated on the Si guiding template fabricated by photolithography. The spin-coated SD45 thin film is annealed in a toluene at 85°C for 90 min. The highly ordered SiO_x line structures with a width of 16 nm are successfully formed within the Si guiding template after RIE etching process with CF₄ and O₂ plasma.